Hideto Miyake

List of Publications by Year in Descending Order

249 papers	3,931 citations	29 h-index	52 g-index
270 ext. papers	4,439 ext. citations	2.1 avg, IF	5.36 L-index

#	Paper	IF	Citations
249	Limits on Astrophysical Antineutrinos with the KamLAND Experiment. *Astrophysical Journal*, **2022**, 925, 14	4.7	2
248	Search for Solar Flare Neutrinos with the KamLAND Detector. *Astrophysical Journal*, **2022**, 924, 103	4.7	1
247	Transcriptome analysis of molecular response to UVC irradiation in zebrafish embryos.. *Ecotoxicology and Environmental Safety*, **2022**, 231, 113211	7	0
246	Reduction of dislocation density in lattice-relaxed Al0.68Ga0.32N film grown on periodical 1 μm spacing AlN pillar concave-convex patterns and its effect on the performance of UV-B laser diodes. *Applied Physics Express*, **2022**, 15, 031004	2.4	2
245	Fabrication of vertical AlGaN-based deep-ultraviolet light-emitting diodes operating at high current density (~43 kA cm⁻²) using a laser liftoff method. *Applied Physics Express*, **2022**, 15, 041006	2.4	0
244	A Search for Correlated Low-energy Electron Antineutrinos in KamLAND with Gamma-Ray Bursts. *Astrophysical Journal*, **2022**, 927, 69	4.7	0
243	Thermal radiation resonating with longitudinal optical phonon from surface micro-stripe structures on metal-gallium nitride and sapphire. *Materials Science in Semiconductor Processing*, **2022**, 147, 106726	4.3	0
242	Rare UV-resistant cells in clonal populations of Escherichia coli.. *Journal of Photochemistry and Photobiology B: Biology*, **2022**, 231, 112448	6.7	0
241	Extremely high internal quantum efficiency of AlGaN-based quantum wells on face-to-face annealed sputter-deposited AlN templates. *Applied Physics Express*, **2021**, 14, 122004	2.4	0
240	Search for Low-energy Electron Antineutrinos in KamLAND Associated with Gravitational Wave Events. *Astrophysical Journal*, **2021**, 909, 116	4.7	3
239	AlGaN Channel High Electron Mobility Transistors with Regrown Ohmic Contacts. *Electronics (Switzerland)*, **2021**, 10, 635	2.6	8
238	AlGaN-based UV-B laser diode with a high optical confinement factor. *Applied Physics Letters*, **2021**, 118, 163504	3.4	11
237	Analysis of carrier injection efficiency of AlGaN UV-B laser diodes based on the relationship between threshold current density and cavity length. *Japanese Journal of Applied Physics*, **2021**, 60, 074002	1.4	4
236	High Electron Mobility AlN on Sapphire (0001) with a Low Dislocation Density Prepared via Sputtering and High-Temperature Annealing. *Physica Status Solidi (A) Applications and Materials Science*, **2021**, 218, 2100074	1.6	0
235	Thick AlN layers grown on micro-scale patterned sapphire substrates with sputter-deposited annealed AlN films by hydride vapor-phase epitaxy. *Journal of Crystal Growth*, **2021**, 566-567, 126163	1.6	1
234	High-Quality AlN Template Prepared by Face-to-Face Annealing of Sputtered AlN on Sapphire. *Physica Status Solidi (B): Basic Research*, **2021**, 258, 2000352	1.3	6
233	High-quality AlN/sapphire templates prepared by thermal cycle annealing for high-performance ultraviolet light-emitting diodes. *Applied Physics Express*, **2021**, 14, 035505	2.4	12

232	Effect of the Sputtering Deposition Conditions on the Crystallinity of High-Temperature Annealed AlN Films. *Coatings*, **2021**, 11, 956	2.9	0
231	The nylon balloon for xenon loaded liquid scintillator in KamLAND-Zen 800 neutrinoless double-beta decay search experiment. *Journal of Instrumentation*, **2021**, 16, P08023	1	4
230	Thermal strain analysis considering in-plane anisotropy for sputtered AlN on c- and a-plane sapphire under high-temperature annealing. *AIP Advances*, **2021**, 11, 095012	1.5	2
229	Effect of MOVPE growth conditions on AlN films on annealed sputtered AlN templates with nano-striped patterns. *Journal of Crystal Growth*, **2021**, 570, 126237	1.6	0
228	Low-threshold-current (~85 mA) of AlGaN-based UV-B laser diode with refractive-index waveguide structure. *Applied Physics Express*, **2021**, 14, 094009	2.4	5
227	Reduction of threading dislocation densities of N-polar face-to-face annealed sputtered AlN on sapphire. *Journal of Crystal Growth*, **2021**, 574, 126309	1.6	3
226	Reduction of dislocation density in Al0.6Ga0.4N film grown on sapphire substrates using annealed sputtered AlN templates and its effect on UV-B laser diodes. *Journal of Crystal Growth*, **2021**, 575, 126325	1.6	4
225	Crystalline quality improvement of face-to-face annealed MOVPE-grown AlN on vicinal sapphire substrate with sputtered nucleation layer. *Journal of Crystal Growth*, **2020**, 545, 125722	1.6	7
224	Effect of dislocation density on optical gain and internal loss of AlGaN-based ultraviolet-B band lasers. *Applied Physics Express*, **2020**, 13, 045504	2.4	10
223	Room-temperature operation of AlGaN ultraviolet-B laser diode at 298 nm on lattice-relaxed Al0.6Ga0.4N/AlN/sapphire. *Applied Physics Express*, **2020**, 13, 031004	2.4	40
222	Internal loss of AlGaN-based ultraviolet-B band laser diodes with p-type AlGaN cladding layer using polarization doping. *Applied Physics Express*, **2020**, 13, 071008	2.4	15
221	Suppression of dislocation-induced spiral hillocks in MOVPE-grown AlGaN on face-to-face annealed sputter-deposited AlN template. *Applied Physics Letters*, **2020**, 116, 062101	3.4	25
220	High Crystallinity and Highly Relaxed Al0.60Ga0.40N Films Using Growth Mode Control Fabricated on a Sputtered AlN Template with High-Temperature Annealing. *Physica Status Solidi (A) Applications and Materials Science*, **2020**, 217, 1900868	1.6	10
219	Individually resolved luminescence from closely stacked GaN/AlN quantum wells. *Photonics Research*, **2020**, 8, 610	6	5
218	Low dislocation density AlN on sapphire prepared by double sputtering and annealing. *Applied Physics Express*, **2020**, 13, 095501	2.4	16
217	MOVPE growth of AlN films on nano-patterned sapphire substrates with annealed sputtered AlN. *Journal of Crystal Growth*, **2020**, 532, 125397	1.6	10
216	Annealing behaviors of vacancy-type defects in AlN deposited by radio-frequency sputtering and metalorganic vapor phase epitaxy studied using monoenergetic positron beams. *Journal of Applied Physics*, **2020**, 128, 085704	2.5	10
215	High-Temperature Annealing of Sputter-Deposited AlN on (001) Diamond Substrate. *Physica Status Solidi (B): Basic Research*, **2020**, 257, 1900447	1.3	2

214	Structural analysis of polarity inversion boundary in sputtered AlN films annealed under high temperatures. *Japanese Journal of Applied Physics*, **2019**, 58, SCCB30	1.4	8
213	Reduction of threading dislocation density and suppression of cracking in sputter-deposited AlN templates annealed at high temperatures. *Applied Physics Express*, **2019**, 12, 065501	2.4	43
212	Ultraviolet-B band lasers fabricated on highly relaxed thick Al0.55Ga0.45N films grown on various types of AlN wafers. *Japanese Journal of Applied Physics*, **2019**, 58, SC1052	1.4	20
211	Local and anisotropic strain in AlN film on sapphire observed by Raman scattering spectroscopy. *Japanese Journal of Applied Physics*, **2019**, 58, SCCB17	1.4	8
210	Improved emission intensity of UVC-LEDs from using strain relaxation layer on sputter-annealed AlN. *Japanese Journal of Applied Physics*, **2019**, 58, SCCC07	1.4	2
209	Preparation of high-quality thick AlN layer on nanopatterned sapphire substrates with sputter-deposited annealed AlN film by hydride vapor-phase epitaxy. *Japanese Journal of Applied Physics*, **2019**, 58, SC1003	1.4	10
208	Deep Ultraviolet Light Source from Ultrathin GaN/AlN MQW Structures with Output Power Over 2 Watt. *Advanced Optical Materials*, **2019**, 7, 1801763	8.1	29
207	Curvature-controllable and crack-free AlN/sapphire templates fabricated by sputtering and high-temperature annealing. *Journal of Crystal Growth*, **2019**, 512, 131-135	1.6	7
206	Quantitative evaluation of strain relaxation in annealed sputter-deposited AlN film. *Journal of Crystal Growth*, **2019**, 512, 16-19	1.6	19
205	Statistics of excitonic energy states based on phononic-excitonic-radiative model. *Japanese Journal of Applied Physics*, **2019**, 58, SCCB34	1.4	3
204	Impact of face-to-face annealed sputtered AlN on the optical properties of AlGaN multiple quantum wells. *AIP Advances*, **2019**, 9, 125342	1.5	9
203	Fabrication of AlN templates on SiC substrates by sputtering-deposition and high-temperature annealing. *Journal of Crystal Growth*, **2019**, 510, 13-17	1.6	11
202	Polarity inversion of aluminum nitride by direct wafer bonding. *Applied Physics Express*, **2018**, 11, 031003	2.4	6
201	Temperature Dependence of Stokes Shifts of Excitons and Biexcitons in Al0.61Ga0.39N Epitaxial Layer. *Physica Status Solidi (B): Basic Research*, **2018**, 255, 1700374	1.3	3
200	AlGaN-based deep UV LEDs grown on sputtered and high temperature annealed AlN/sapphire. *Applied Physics Letters*, **2018**, 112, 041110	3.4	136
199	Microstructural analysis in the depth direction of a heteroepitaxial AlN thick film grown on a trench-patterned template by nanobeam X-ray diffraction. *Journal of Applied Physics*, **2018**, 123, 161563	2.5	1
198	Growth of High-Quality AlN and AlGaN Films on Sputtered AlN/Sapphire Templates via High-Temperature Annealing. *Physica Status Solidi (B): Basic Research*, **2018**, 255, 1700506	1.3	26
197	Temperature dependence of excitonic transitions in Al0.60Ga0.40N/Al0.70Ga0.30N multiple quantum wells from 4 to 750 K. *Journal of Applied Physics*, **2018**, 123, 205705	2.5	4

196	Growth of Si-doped AlN on sapphire (0001) via pulsed sputtering. *APL Materials*, **2018**, 6, 111103	5.7	5
195	Improvement mechanism of sputtered AlN films by high-temperature annealing. *Journal of Crystal Growth*, **2018**, 502, 41-44	1.6	50
194	Selective area growth of GaN on trench-patterned nonpolar bulk GaN substrates. *Journal of Crystal Growth*, **2017**, 468, 851-855	1.6	1
193	A design strategy for achieving more than 90% of the overlap integral of electron and hole wavefunctions in high-AlN-mole-fraction AlxGa1□N multiple quantum wells. *Applied Physics Express*, **2017**, 10, 015802	2.4	10
192	High-temperature photoluminescence and photoluminescence excitation spectroscopy of Al0.60Ga0.40N/Al0.70Ga0.30N multiple quantum wells. *Applied Physics Express*, **2017**, 10, 021002	2.4	7
191	Confinement-enhanced biexciton binding energy in AlGaN-based quantum wells. *Applied Physics Express*, **2017**, 10, 051003	2.4	2
190	High-quality and highly-transparent AlN template on annealed sputter-deposited AlN buffer layer for deep ultra-violet light-emitting diodes. *AIP Advances*, **2017**, 7, 055110	1.5	35
189	Structural study of GaN grown on nonpolar bulk GaN substrates with trench patterns. *Japanese Journal of Applied Physics*, **2017**, 56, 125504	1.4	1
188	Fabrication of high-crystallinity a -plane AlN films grown on r -plane sapphire substrates by modulating buffer-layer growth temperature and thermal annealing conditions. *Journal of Crystal Growth*, **2017**, 468, 845-850	1.6	16
187	Preparation of high-quality AlN on sapphire by high-temperature face-to-face annealing. *Journal of Crystal Growth*, **2016**, 456, 155-159	1.6	165
186	Annealing of an AlN buffer layer in N2□O for growth of a high-quality AlN film on sapphire. *Applied Physics Express*, **2016**, 9, 025501	2.4	139
185	Microstructural analysis of an epitaxial AlN thick film/trench-patterned template by three-dimensional reciprocal lattice space mapping technique. *Applied Physics Express*, **2016**, 9, 111001	2.4	6
184	Impact of high-temperature annealing of AlN layer on sapphire and its thermodynamic principle. *Japanese Journal of Applied Physics*, **2016**, 55, 05FL02	1.4	36
183	Excitation and deexcitation dynamics of excitons in a GaN film based on the analysis of radiation from high-order states. *Journal Physics D: Applied Physics*, **2016**, 49, 245102	3	4
182	Reduction of dislocation density of aluminium nitride buffer layer grown on sapphire substrate. *Journal of Mechanical Engineering and Sciences*, **2016**, 10, 1908-1916	2	2
181	Microscopic potential fluctuations in Si-doped AlGaN epitaxial layers with various AlN molar fractions and Si concentrations. *Journal of Applied Physics*, **2016**, 119, 025707	2.5	5
180	Growth and characterization of Cu2ZnSn(S Se1□)4 single crystal grown by traveling heater method. *Journal of Crystal Growth*, **2015**, 423, 9-15	1.6	10
179	Solution growth of chalcopyrite compounds single crystal. *Renewable Energy*, **2015**, 79, 127-130	8.1	5

178	HVPE homoepitaxy on freestanding AlN substrate with trench pattern. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2015**, 12, 334-337		3
177	Using surface-plasmon polariton at the GaP-Au interface in order to detect chemical species in high-refractive-index media. *Optics Communications*, **2015**, 341, 64-68	2	8
176	Microscopic crystalline structure of a thick AlN film grown on a trench-patterned AlN/□Al2O3 template. *Journal of Crystal Growth*, **2015**, 411, 38-44	1.6	8
175	Reduction in the concentration of cation vacancies by proper Si-doping in the well layers of high AlN mole fraction AlxGa1□xN multiple quantum wells grown by metalorganic vapor phase epitaxy. *Applied Physics Letters*, **2015**, 107, 121602	3.4	21
174	Fabrication of AlGaN multiple quantum wells on sapphire with lattice-relaxation layer. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2015**, 12, 361-364		
173	Growth Characteristics of Graphene Film by Chemical Vapor Deposition Method Using Nozzle Gas Injection. *E-Journal of Surface Science and Nanotechnology*, **2015**, 13, 265-268	0.7	
172	Study on AlN growth conditions for hydride vapor phase epitaxy. *Transactions of the Materials Research Society of Japan*, **2015**, 40, 395-396	0.2	
171	Excitation-dependent carrier dynamics in Al-rich AlGaN layers and multiple quantum wells. *Physica Status Solidi (B): Basic Research*, **2015**, 252, 1043-1049	1.3	3
170	Extraordinary Optical Transmission Exhibited by Surface Plasmon Polaritons in a Double-Layer Wire Grid Polarizer. *Plasmonics*, **2015**, 10, 1657-1662	2.4	13
169	Thermo-physical properties of Cu2ZnSnS4 single crystal. *Journal of Crystal Growth*, **2014**, 393, 167-170	1.6	17
168	Growth and characterization of Cu2ZnSn(S Se1□)4 alloys grown by the melting method. *Journal of Crystal Growth*, **2014**, 386, 204-207	1.6	18
167	Properties of GaN grown on Si(111) substrates dependent on the thickness of 3C-SiC intermediate layers. *Journal of Applied Physics*, **2014**, 115, 063102	2.5	6
166	Effects of sodium on electrical properties in Cu2ZnSnS4 single crystal. *Applied Physics Letters*, **2014**, 104, 152101	3.4	100
165	Growth of AlN Crystals on SiC Substrates by Thermal Nitridation of Al2O3. *Journal of the American Ceramic Society*, **2014**, 97, 3781-3786	3.8	2
164	Inhomogeneous distribution of defect-related emission in Si-doped AlGaN epitaxial layers with different Al content and Si concentration. *Journal of Applied Physics*, **2014**, 115, 053509	2.5	19
163	Crack-free GaN grown by using maskless epitaxial lateral overgrowth on Si substrate with thin SiC intermediate layer. *Physica Status Solidi (A) Applications and Materials Science*, **2014**, 211, 744-747	1.6	3
162	Binding energy of localized biexcitons in AlGaN-based quantum wells. *Applied Physics Express*, **2014**, 7, 122101	2.4	7
161	Anisotropic crystalline morphology of epitaxial thick AlN films grown on triangular-striped AlN/sapphire template. *Physica Status Solidi (A) Applications and Materials Science*, **2014**, 211, 731-735	1.6	3

160	Transient photoluminescence of aluminum-rich (Al,Ga)N low-dimensional structures. *Physica Status Solidi (A) Applications and Materials Science*, **2014**, 211, 765-768	1.6	5
159	Si concentration dependence of structural inhomogeneities in Si-doped AlxGa1−xN/AlyGa1−yN multiple quantum well structures (x = 0.6) and its relationship with internal quantum efficiency. *Journal of Applied Physics*, **2014**, 116, 235703	2.5	4
158	Cross-sectional X-ray microdiffraction study of a thick AlN film grown on a trench-patterned AlN/□Al2O3 template. *Journal of Crystal Growth*, **2013**, 381, 37-42	1.6	9
157	Growth and characterization of Cu2ZnSnS4 single crystals. *Physica Status Solidi (A) Applications and Materials Science*, **2013**, 210, 1328-1331	1.6	22
156	Correlation between intrinsic defects and electrical properties in the high-quality Cu2ZnSnS4 single crystal. *Applied Physics Letters*, **2013**, 103, 112107	3.4	67
155	Study on the effects of AlN interlayer in thick GaN grown on 3C-SiC/Si substrates. *Journal of Crystal Growth*, **2013**, 370, 254-258	1.6	4
154	Nanoindentation hardness and elastic modulus of AlGaN alloys **2013**,		1
153	Effects of Si doping in high-quality AlN grown by MOVPE on trench-patterned template. *Journal of Crystal Growth*, **2013**, 370, 74-77	1.6	3
152	Impacts of Si-doping and resultant cation vacancy formation on the luminescence dynamics for the near-band-edge emission of Al0.6Ga0.4N films grown on AlN templates by metalorganic vapor phase epitaxy. *Journal of Applied Physics*, **2013**, 113, 213506	2.5	73
151	AlN Grown ona- andn-Plane Sapphire Substrates by Low-Pressure Hydride Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **2013**, 52, 08JB31	1.4	10
150	Growth and Characterization of AlGaN Multiple Quantum Wells for Electron-Beam Target for Deep-Ultraviolet Light Sources. *Japanese Journal of Applied Physics*, **2013**, 52, 01AF03	1.4	23
149	Correlation between in-plane strain and optical polarization of Si-doped AlGaN epitaxial layers as a function of Al content and Si concentration. *Journal of Applied Physics*, **2012**, 112, 033512	2.5	8
148	AlN homoepitaxial growth on sublimation-AlN substrate by low-pressure HVPE. *Journal of Crystal Growth*, **2012**, 350, 69-71	1.6	14
147	Preparation of Cu2ZnSnS4 single crystals from Sn solutions. *Journal of Crystal Growth*, **2012**, 341, 38-41	1.6	59
146	Growth of Cu2ZnSnSe4 single crystals from Sn solutions. *Journal of Crystal Growth*, **2012**, 354, 147-151	1.6	40
145	Native cation vacancies in Si-doped AlGaN studied by monoenergetic positron beams. *Journal of Applied Physics*, **2012**, 111, 013512	2.5	45
144	Orientation dependence of polarized Raman spectroscopy for nonpolar, semi-polar, and polar bulk GaN substrates. *Applied Physics Letters*, **2012**, 100, 011909	3.4	10
143	Strain control of GaN grown on 3C-SiC/Si substrate using AlGaN buffer layer. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 550-553		5

142	Effects of carrier gas ratio and growth temperature on MOVPE growth of AlN. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 499-502		12
141	Fabrication of crack-free thick AlN film on a-plane sapphire by low-pressure HVPE. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 576-579		7
140	Photoluminescence due to Inelastic Biexciton Scattering from an Al$_{0.61}$Ga$_{0.39}$N Ternary Alloy Epitaxial Layer at Room Temperature. *Applied Physics Express*, **2012**, 5, 072401	2.4	8
139	Temperature Dependence of Linear Thermal Expansion of CuGaSe2 Crystals. *Materials Science Forum*, **2012**, 725, 171-174	0.4	1
138	Dependence of internal quantum efficiency on doping region and Si concentration in Al-rich AlGaN quantum wells. *Applied Physics Letters*, **2012**, 101, 042110	3.4	37
137	Observation of longitudinal-optic-phonon-plasmon-coupled mode in n-type AlGaN alloy films. *Applied Physics Letters*, **2011**, 99, 251904	3.4	5
136	HVPE growth of c-plane AlN on a-plane sapphire using nitridation layer. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 470-472		6
135	HVPE growth of AlN on trench- patterned 6H-SiC substrates. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 467-469		9
134	Recombination dynamics of localized excitons in AlxGa1-xN (0.37. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2133-2135		5
133	Evidence for moving of threading dislocations during the VPE growth in GaN thin layers. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 1487-1490		4
132	HVPE growth of thick AlN on trench-patterned substrate. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 1483-1486		7
131	Control of AlN buffer/sapphire substrate interface for AlN growth. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2069-2071		16
130	Huge binding energy of localized biexcitons in Al-rich AlxGa1⊠N ternary alloys. *Applied Physics Letters*, **2011**, 98, 081907	3.4	8
129	Silicon concentration dependence of optical polarization in AlGaN epitaxial layers. *Applied Physics Letters*, **2011**, 98, 021910	3.4	14
128	Fabrication of Deep-Ultraviolet-Light-Source Tube Using Si-Doped AlGaN. *Applied Physics Express*, **2011**, 4, 042103	2.4	52
127	Growth of High-Quality Si-Doped AlGaN by Low-Pressure Metalorganic Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **2011**, 50, 095502	1.4	13
126	Growth of Cu2ZnSnS4Single Crystal by Traveling Heater Method. *Japanese Journal of Applied Physics*, **2011**, 50, 128001	1.4	3
125	Variation of Surface Potentials of Si-Doped AlxGa1-xN (0 . *Applied Physics Express*, **2010**, 3, 021004	2.4	5

124	Deep Electronic Levels of AlxGa1-xN with a Wide Range of Al Composition Grown by Metal Organic Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **2010**, 49, 101001	1.4	9
123	In-plane structural anisotropy and polarized Raman-active mode studies of nonpolar AlN grown on 6H-SiC by low-pressure hydride vapor phase epitaxy. *Journal of Crystal Growth*, **2010**, 312, 490-494	1.6	7
122	Formation mechanism of Al-depleted bands in MOVPE-AlGaN layer on GaN template with trenches. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2010**, 7, 2036-2039		
121	a -plane AlN and AlGaN growth on r -plane sapphire by MOVPE. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2010**, 7, 2107-2110		5
120	In-plane electric field induced by polarization and lateral photovoltaic effect in a-plane GaN. *Applied Physics Letters*, **2009**, 94, 231102	3.4	7
119	Growth of High Quality c-plane AlN on a-plane Sapphire. *Materials Research Society Symposia Proceedings*, **2009**, 1202, 55		1
118	Facet-control in selective area growth (SAG) of a-plane GaN by MOVPE. *Materials Research Society Symposia Proceedings*, **2009**, 1202, 98		
117	Fabrication of a binary diffractive lens for controlling the luminous intensity distribution of LED light. *Optical Review*, **2009**, 16, 455-457	0.9	6
116	Effects of initial conditions and growth temperature on the properties of nonpolar a -plane AlN grown by LP-HVPE. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, S478-S481		5
115	Mobility enhancement of 2DEG in MOVPE-grown AlGaN/AlN/GaN HEMT structure using vicinal (0 0 0 1) sapphire. *Superlattices and Microstructures*, **2009**, 46, 812-816	2.8	9
114	Low-pressure HVPE growth of crack-free thick AlN on a trench-patterned AlN template. *Journal of Crystal Growth*, **2009**, 311, 2831-2833	1.6	36
113	Structural and electrical properties of Si-doped a-plane GaN grown on r-plane sapphire by MOVPE. *Journal of Crystal Growth*, **2009**, 311, 2899-2902	1.6	18
112	Photoluminescence study of Si-doped a-plane GaN grown by MOVPE. *Journal of Crystal Growth*, **2009**, 311, 2906-2909	1.6	19
111	Optical properties of MOVPE-grown a-plane GaN and AlGaN. *Journal of Crystal Growth*, **2009**, 311, 2903-2905	1.6	9
110	Growth of undoped and Zn-doped GaN nanowires. *Journal of Crystal Growth*, **2009**, 311, 2970-2972	1.6	9
109	Effects of initial stages on the crystal quality of nonpolar a-plane AlN on r-plane sapphire by low-pressure HVPE. *Journal of Crystal Growth*, **2009**, 311, 3801-3805	1.6	18
108	Influence of off-cut angle of r-plane sapphire on the crystal quality of nonpolar a-plane AlN by LP-HVPE. *Journal of Crystal Growth*, **2009**, 311, 4473-4477	1.6	17
107	Effects of Substrate Plane on the Growth of High Quality AlN by Hydride Vapor Phase Epitaxy. *Applied Physics Express*, **2009**, 2, 111004	2.4	16

106	Nitridating r-plane sapphire to improve crystal qualities and surface morphologies of a-plane GaN grown by metalorganic vapor phase epitaxy. *Applied Physics Letters*, **2009**, 95, 121910	3.4	19
105	Effect of strain on quantum efficiency of InAlN-based solar-blind photodiodes. *Applied Physics Letters*, **2009**, 95, 083504	3.4	17
104	Transmission Electron Microscopy Characterization of Position-Controlled InN Nanocolumns. *Japanese Journal of Applied Physics*, **2008**, 47, 5330-5332	1.4	18
103	Thermal analysis of GaN powder formation via reaction of gallium ethylenediamine tetraacetic acid complexes with ammonia. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 1522-1524		1
102	Improved surface morphology of flow-modulated MOVPE grown AlN on sapphire using thin medium-temperature AlN buffer layer. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 1818-1821		0
101	Improved optical properties of AlGaN using periodic structures. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 1822-1824		1
100	Reactor-pressure dependence of growth of a-plane GaN on r-plane sapphire by MOVPE. *Journal of Crystal Growth*, **2008**, 310, 4979-4982	1.6	31
99	Growth of crack-free AlGaN on selective-area-growth GaN. *Journal of Crystal Growth*, **2008**, 310, 4885-4887		7
98	Optical Characterization of Japanese Papers for Application in the LED Lighting System with Human Sensitivity. *Journal of Light and Visual Environment*, **2008**, 32, 218-221		1
97	Selective Area Growth of III-Nitride and Their Application for Emitting Devices. *Journal of Light and Visual Environment*, **2008**, 32, 177-182		
96	Improved surface morphology of flow-modulated MOVPE grown AlN on sapphire using thin medium-temperature AlN buffer layer. *Applied Surface Science*, **2007**, 253, 9395-9399	6.7	4
95	Influence of growth conditions on Al incorporation to AlxGa1−xN (x>0.4) grown by MOVPE. *Journal of Crystal Growth*, **2007**, 298, 372-374	1.6	13
94	Influence of growth interruption and Si doping on the structural and optical properties of AlxGaN/AlN (x>0.5) multiple quantum wells. *Journal of Crystal Growth*, **2007**, 298, 500-503	1.6	14
93	Synthesis of III-nitride microcrystals using metal-EDTA complexes. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2007**, 4, 2346-2349		4
92	Dependence of In mole fraction in InGaN on GaN facets. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2007**, 4, 2383-2386		1
91	High temperature growth of AlN film by LP-HVPE. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2007**, 4, 2252-2255		17
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